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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Complete If Known	
		Application Number	10/604,747
		Filing Date	August 14, 2003
		First Named Inventor	Herr, Daniel J seph Christian
		Art Unit	
Sheet 1 of	Examiner Name	Attorney Docket Number	361007-000025

U.S. PATENT DOCUMENTS						
Examiner Initials ¹	Cite No. ¹	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)				
MW	AA	5,787,253		7/28/98	McCreery et al.	
MW	AB	6,068,698		5/30/00	Schmidt	
MW	AV	5,981,316		11/09/99	Yamada et al.	

FOREIGN PATENT DOCUMENTS						
Examiner Initials ¹	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ² -Number ³ -Kind Code ⁴ (If known)				
MW	AC	99/13511	3-18-99	Schmidt		
MW	AD	0,781,727	2-7-97	NEC Corp.		

NON PATENT LITERATURE DOCUMENTS		
Examiner Initial	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
MW	AE	D. M. Eigler et al., "Positioning single atoms with a scanning tunnelling microscope", <i>Nature</i> , Vol. 344 (April 1990) pp 524-526.
MW	AF	P. Bedrossian et al., "Demonstration of the tunnel-diode effect on an atomic", scale, <i>Nature</i> , Vol. 342 (November 1989) pp 258-260.
MW	AG	Nishi Y. ET AL., <i>Handbook of Semiconductor Manufacturing Technology</i> , Marcel Dekker, Inc. New York, NY (2000).
MW	AH	Frank, D. et al., "Device Scaling Limits of SiMOSFETs and Their Application Dependencies," <i>Proceedings of the IEEE</i> , Vol. 89, No. 3, (March 2001).
MW	AI	Gross, W. et al., "Ultrasmall MOSFETs: The Importance of the full Coulomb Interaction on Device Characteristics," <i>IEEE Transactions on Electron Devices</i> , Vol. 47, No. 10, (October 2000).
MW	AJ	Clark, A., "Russian Technology Waves Goodbye to Strained Silicon," <i>EE Times</i> , (April 8, 2002).

Examiner Signature	MWilewski	Date Considered	9/2004
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 1 Applicant's unique citation designation number (optional). 2 See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. 3 Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). 4 For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. 5 Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. 6 Applicant is to place a check mark here if English language Translation is attached. This collection of information is required by 37 CFR 1.97 and 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

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Substitute for form 1449B/PTO		C mplete If Known	
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Sheet 2 of 2	Attorney Docket Number	361007-000025	

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
MW	AK	Feynman, R.P., Infinitesimal Machinery, <i>Journal of MicroMechanical Systems</i> , Vol. 2, No. 1, March 1993, pp. 4-14.	
MW	AL	Feynman, R.P., "There's Plenty of Room at the Bottom", <i>Engineering and Science</i> , Vol. 23, 1960, pp. 22-36, Reprinted in Anthony J.G. Hey (Ed.), <i>Feynman and Computation: Exploring the Limits of Computers</i> , Perseus Books, 1990.	
MW	AM	Giro, et al., "Single Layer Electroluminescent Devices Based on Molecularly Doped Polymer", (MDP) Films, <i>Synthetic Metals</i> , Vol. 84, 1997, pp. 379-80.	
MW	AN	Johnson, et al., "Electroluminescence From Single Layer Molecularly Doped Polymer Films", <i>SPIE</i> , Vol. 1910, 1993, pp. 6-14.	
MW	AO	Metzger, R.M., "Electrical Rectification by a Molecule: The Advent of Unimolecular Electronic Devices", <i>Accounts of Chemical Research</i> , Vol. 32, No. 11, 1999, pp. 950-7.	
MW	AP	Nikzad, et al., "Direct Detection and Imaging of Low-Energy Electrons With Delta-Doped Charge-Coupled Devices", <i>Applied Physics Letters</i> , Vol. 73, No. 23, December 7, 1998, pp. 3417-9.	
MW	AQ	Stormer, et al., "GaAs Field-Effect Transistor With An Atomically Precise Ultrashort Gate", <i>Appl. Phys. Lett.</i> , Vol. 59, No. 9, August 26, 1991, pp. 1111-3.	
MW	AR	Tucker, et al., "Prospects for Atomically Ordered Device Structures Based on STM Lithography", <i>Solid-State Electronics</i> , Vol. 42, No. 7-8, 1998, pp. 1061-7.	
MW	AS	Zaknounge, et al., "High-Power V-Band Ga _{0.51} In _{0.49} P/In _{0.2} Ga _{0.8} As Pseudomorphic HEMT Grown by Gas Source Molecular Beam Epitaxy", <i>IEEE Microwave and Guided Wave Letters</i> , Vol. 9, No. 1, January 1999, pp. 28-30.	
MW	AT	Saito, S. et al., "Electronic Structure of Si ₂₀ and C ₂₀ Fullerenes," <i>Proceedings of the Symposium on Recent Advances in the Chemistry and Physics of Fullerenes and Related Materials</i> , Vol. 3, pp. 457-461, 1996.	
MW	AU	Cavin, R. et al., "Semiconductor research needs in the nanoscale physical sciences: a Semiconductor Research Corporation working paper," <i>Journal of Nanoparticle Research</i> 2; pp. 213-235; 2000.	
MW	AV	Ozin, Geoffrey A.; "Nanotechnology: Synthesis in Diminishing Dimensions," <i>Advanced Materials</i> 4, No. 10; pp.612-649; 1992.	
MW	AW	Desiraju, G.R. (Ed.), "Thoughts on Crystals as Supramolecules", <i>The Crystal as a Supramolecular Entity</i> , John Wiley and Sons Ltd., 1996.	
MW	AX	Zhirnov et al., "On Designing Sub-70-nm Semiconductor Materials and Processes," <i>IEEE Transactions on Semiconductor Manufacturing</i> , Vol. 15, No. 2 (May 2002).	

Examiner Signature	MW/Lezewski	Date Considered	9/2004
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